



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-523 Plastic-Encapsulate Diodes

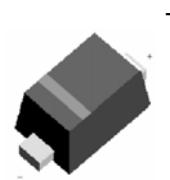
BAP51-02 GENERAL PURPOSE PIN DIODES

FEATURES

- Low diode capacitance
- Low diode forward resistance

MARKING: A5

SOD-523



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

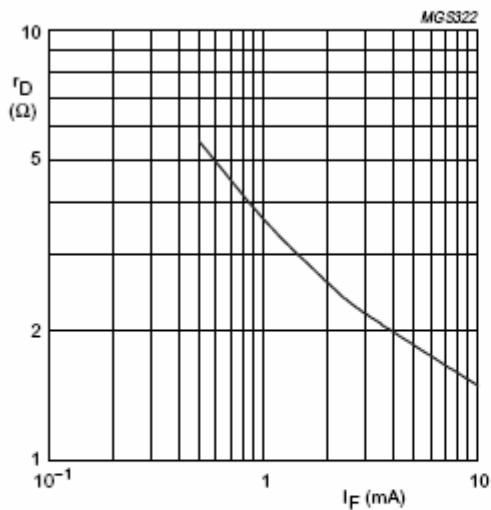
Parameter	Symbol	Limits		Unit
Continuous reverse voltage	V _R	60		V
Continuous Forward Current	I _F	50		mA
Power Dissipation (T _A =90°C)	P _d	715		mW
Thermal Resistance from Junction to soldering point	R _{θJS}	85		°C/W
Junction temperature	T _j	-65~+150		°C
Storage temperature	T _{STG}	-65~+150		°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Continuous reverse voltage	V _R	50			V	I _R =10µA
Forward voltage	V _F			1.1	V	I _F =50mA
Reverse current	I _R			100	nA	V _R =50V
Diode capacitance	C _{d1}		0.4*		pF	V _R =0V,f=1MHz
	C _{d2}			0.55	pF	V _R =1V,f=1MHz
	C _{d3}			0.35	pF	V _R =5V,f=1MHz
Diode forward resistance	r _D			9	Ω	I _F =0.5mA , f=100MHz
	r _D			6.5	Ω	I _F =1mA , f=100MHz
	r _D			2.5	Ω	I _F =10mA , f=100MHz

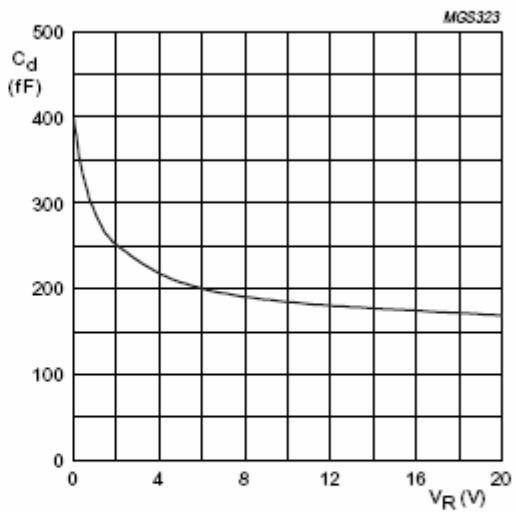
Typical Characteristics

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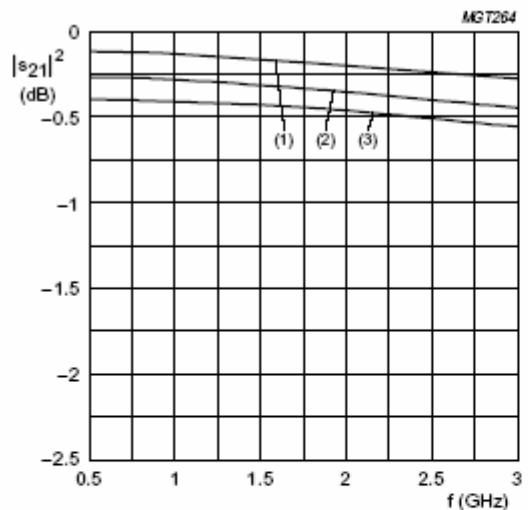
$f = 100 \text{ MHz}; T_j = 25^\circ\text{C}.$

Fig.2 Forward resistance as a function of forward current; typical values.



$f = 1 \text{ MHz}; T_j = 25^\circ\text{C}.$

Fig.3 Diode capacitance as a function of reverse voltage; typical values.

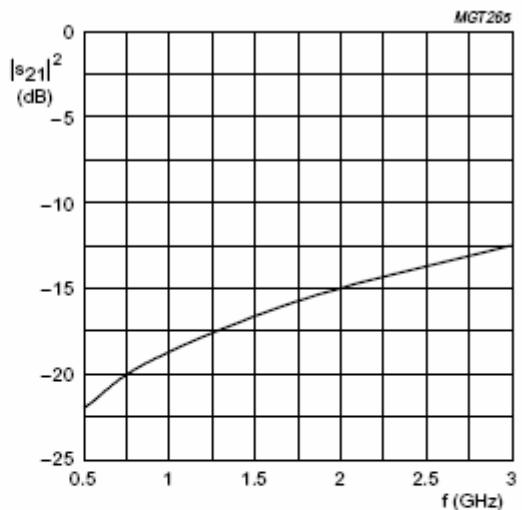


(1) $I_F = 10 \text{ mA}$. (2) $I_F = 1 \text{ mA}$. (3) $I_F = 0.5 \text{ mA}$.

Diode inserted in series with a 50Ω stripline circuit and biased via the analyzer Tee network.

$T_{\text{amb}} = 25^\circ\text{C}.$

Fig.4 Insertion loss ($|s_{21}|^2$) of the diode as a function of frequency; typical values.



Diode zero biased and inserted in series with a 50Ω stripline circuit.
 $T_{\text{amb}} = 25^\circ\text{C}.$

Fig.5 Isolation ($|s_{21}|^2$) of the diode as a function of frequency; typical values.